

L Number	Hits	Search Text	DB	Time stamp
11	314	"liner oxide"	USPAT; US-PGPUB	2002/05/31 12:58
14	1	("5,651,899").PN.	USPAT; US-PGPUB	2002/05/31 12:59
17	266	"liner oxide" and trench	USPAT; US-PGPUB	2002/05/31 13:10
26	7630	STI or "shallow trench" or "trench isolation"	USPAT; US-PGPUB	2002/05/31 13:10
29	956	((STI or "shallow trench" or "trench isolation") and SOI	USPAT; US-PGPUB	2002/05/31 13:11
69	461	((STI or "shallow trench" or "trench isolation") and SOI) and (insulating ADJ2 layer)	USPAT; US-PGPUB	2002/05/31 13:11
75	371	((STI or "shallow trench" or "trench isolation") and SOI) and (insulating ADJ2 layer)) and gate	USPAT; US-PGPUB	2002/05/31 13:35
78	303	((STI or "shallow trench" or "trench isolation") and SOI) and (insulating ADJ2 layer)) and gate) and (BPSG or TEOS or dielectric)	USPAT; US-PGPUB	2002/05/31 13:35
81	17	((STI or "shallow trench" or "trench isolation") and SOI) and ((insulating ADJ2 layer) SAME (BPSG or TEOS or dielectric))	USPAT; US-PGPUB	2002/05/31 13:45
84	150	((STI or "shallow trench" or "trench isolation") and SOI) and ((insulating ADJ2 layer) SAME (BPSG or TEOS or dielectric)) and gate	USPAT; US-PGPUB	2002/05/31 13:45
87	41	((STI or "shallow trench" or "trench isolation") and SOI) and ((insulating ADJ2 layer) SAME (BPSG or TEOS or dielectric)) and gate) and FET	USPAT; US-PGPUB	2002/05/31 13:45
90	59	((STI or "shallow trench" or "trench isolation") and SOI) and ((insulating ADJ2 layer) SAME (BPSG or TEOS or dielectric) SAME (thickness or angstrom or ang))	USPAT; US-PGPUB	2002/05/31 14:00
93	26	((STI or "shallow trench" or "trench isolation") and SOI) and ((insulating ADJ2 layer) SAME (BPSG or TEOS or dielectric) SAME (thickness or angstrom or ang)) and FET	USPAT; US-PGPUB	2002/05/31 15:19
96	1	("8368941").PN.	USPAT; US-PGPUB	2002/05/31 15:19
-	18700	"body contact" or "floating body" or "substrate contact"	USPAT; US-PGPUB	2002/05/29 11:31
-	441	((STI or "shallow trench" or "trench isolation") and ("body contact" or "floating body" or "substrate contact"))	USPAT; US-PGPUB	2002/05/29 11:31
-	164	((STI or "shallow trench" or "trench isolation") and ("body contact" or "floating body" or "substrate contact")) and SOI	USPAT; US-PGPUB	2002/05/29 15:52
-	946	((STI or "shallow trench" or "trench isolation") and (SOI or "silicon on insulator" or "semiconductor on insulator"))	USPAT; US-PGPUB	2002/05/29 16:32
-	738	((STI or "shallow trench" or "trench isolation") and (SOI or "silicon on insulator" or "semiconductor on insulator")) and gate	USPAT; US-PGPUB	2002/05/29 15:59
-	778	((STI or "shallow trench" or "trench isolation") and (SOI or "silicon on insulator" or "semiconductor on insulator") and gate) and oxide	USPAT; US-PGPUB	2002/05/29 16:23
-	490	((STI or "shallow trench" or "trench isolation") and (SOI or "silicon on insulator" or "semiconductor on insulator")) and gate) and oxide) and ("hard mask" or "silicon nitride")	USPAT; US-PGPUB	2002/05/29 16:23
-	9075	STI or ((shallow or deep) ADJ3 trenches) or "trench isolation"	USPAT; US-PGPUB	2002/05/29 16:31

-	6424	SOI or "silicon on insulator" or "semiconductor on insulator"	USPAT; US-PGPUB	2002/05/29 18:32
-	1103	((STI or ((shallow or deep) ADJ3 trenches) or "trench isolation") and (SOI or "silicon on insulator" or "semiconductor on insulator"))	USPAT; US-PGPUB	2002/05/29 18:31
-	1	("5584133").PN.	USPAT; US-PGPUB	2002/05/29 18:39
-	186	((STI or ((shallow or deep) ADJ3 trenches) or "trench isolation") and (SOI or "silicon on insulator" or "semiconductor on insulator")) and ("body contact" or "floating body" or "substrate contact")	USPAT; US-PGPUB	2002/05/30 12:22
-	1116	((STI or ((shallow or deep) ADJ3 trenches) or "trench isolation") and (SOI or "silicon on insulator" or "semiconductor on insulator"))	USPAT; US-PGPUB	2002/05/30 18:49
-	1084	((STI or ((shallow or deep) ADJ3 trenches) or "trench isolation") and (SOI or "silicon on insulator" or "semiconductor on insulator")) and oxide	USPAT; US-PGPUB	2002/05/30 12:25
-	619	((STI or ((shallow or deep) ADJ3 trenches) or "trench isolation") and (SOI or "silicon on insulator" or "semiconductor on insulator")) and oxide and ("silicon nitride")	USPAT; US-PGPUB	2002/05/30 18:39
-	1	("5,656,343") or ("5,691,776").PN.	USPAT; US-PGPUB	2002/05/30 12:38
-	0	"hebert et al." and "silicon nitride"	USPAT; US-PGPUB	2002/05/30 12:38
-	120	((STI or ((shallow or deep) ADJ3 trenches) or "trench isolation") and (SOI or "silicon on insulator" or "semiconductor on insulator")) and oxide and ("hard mask")	USPAT; US-PGPUB	2002/05/30 12:42
-	1	"5693933").PN.	USPAT; US-PGPUB	2002/05/30 12:43
-	2	("5006482"   "5173439").PN.	USPAT	2002/05/30 14:19
-	8	5362541.UF.PN.	USPAT	2002/05/30 14:22
-	864	PTI or "partial trench isolation"	USPAT; US-PGPUB	2002/05/30 16:07
-	15	(PTI or "partial trench isolation") and SOI	USPAT; US-PGPUB	2002/05/30 18:39
-	101	428/FOR.196.cols.	EPO; JPO; DEFWENT	2002/05/30 16:47
-	503	SOI and trench	EPO; JPO; DEFWENT	2002/05/30 18:47
-	95	STI or ((shallow or deep) ADJ3 trenches) or "trench isolation") and (SOI or "silicon on insulator" or "semiconductor on insulator"))	EPO; JPO; DEFWENT	2002/05/31 16:49

L Number	Hits	Search Text	DB	Time stamp
1	0	sti with liner with soi	USPAT; US-PGPUB	2002/05/31 15:03
2	3586	sti	USPAT; US-PGPUB	2002/05/31 15:03
3	59343	liner	USPAT; US-PGPUB	2002/05/31 15:03
4	6435	soi	USPAT; US-PGPUB	2002/05/31 15:03
5	90	sti with liner	USPAT; US-PGPUB	2002/05/31 15:03
6	9	(sti with liner) and soi	USPAT; US-PGPUB	2002/05/31 15:04